## UNISONIC TECHNOLOGIES CO., LTD

### UTG30N120-G2

#### Insulated Gate Bipolar Transistor

# 1200V TRENCH GATE FIELD-STOP IGBT

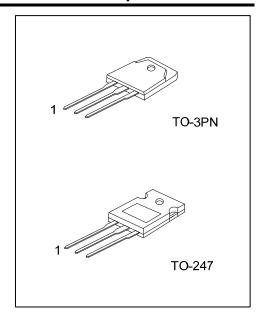
#### **■** DESCRIPTION

The UTC **UTG30N120-G2** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

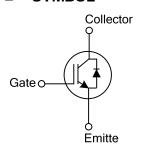
The UTC **UTG30N120-G2** is suitable for the resonant or soft switching applications.

#### **■ FEATURES**

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage: V<sub>CE(sat), typ</sub> =1.82V @ I<sub>C</sub>=30A (T<sub>C</sub> =25°C)
- \* Low switching loss:  $E_{OFF, typ}$ =2.28mJ @  $I_{C}$ =30A ( $T_{C}$  =25°C)

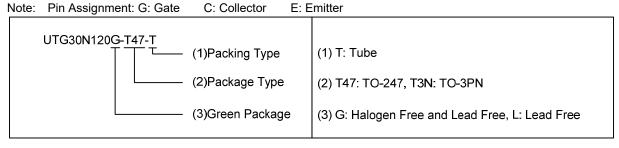


#### ■ SYMBOL

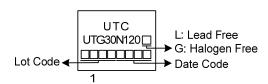


#### **■ ORDERING INFORMATION**

| Ordering Number  |                  | Daalsana | Pin Assignment |   |   | Deelsing |  |
|------------------|------------------|----------|----------------|---|---|----------|--|
| Lead Free        | Halogen Free     | Package  | 1              | 2 | 3 | Packing  |  |
| UTG30N120L-T47-T | UTG30N120G-T47-T | TO-247   | G              | С | Е | Tube     |  |
| UTG30N120L-T3N-T | UTG30N120G-T3N-T | TO-3PN   | G              | С | Е | Tube     |  |



#### **■ MARKING**



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#### **■ ABSOLUTE MAXIMUM RATINGS**

| PARAMETER  |                       | SYMBOL           | RATINGS    | UNIT |
|--|-----------------------|------------------|------------|------|
| Collector-Emitter Voltage  |                       | $V_{CES}$        | 1200       | V    |
| Gate-Emitter Voltage   |                       | $V_{GES}$        | ±20        | V    |
| 0  | T <sub>C</sub> =25°C  | Ic               | 60         | Α    |
| Continuous Collector Current   | T <sub>C</sub> =100°C |                  | 30         | Α    |
| Collector Current Pulsed (Note 1)  |                       | I <sub>CM</sub>  | 100        | Α    |
| Diada Famurad Ormant   | T <sub>C</sub> =25°C  |                  | 60         | Α    |
| Diode Forward Current  | T <sub>C</sub> =100°C | l <sub>F</sub>   | 30         | Α    |
| Short Circuit Withstand Time $V_{GE} = 15V$ , $V_{CC} \le 200V$ Allowed number of short circuits < 1000 Time between short circuits: $\ge$ 1.0s $T_{V,I} = 25^{\circ}$ C |                       | tsc              | 10         | μs   |
| Power Dissipation T <sub>C</sub> =25   | TO-247 TO-3PN         | $P_D$            | 260<br>285 | W    |
| Operating Junction Temperature   |                       | TJ               | -40 ~ +175 | °C   |
| Storage Temperature Range  |                       | T <sub>STG</sub> | -55 ~ +175 | °C   |

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

#### **■ THERMAL DATA**

| PARAMETER         |        | SYMBOL | RATING | UNIT |
|-------------------|--------|--------|--------|------|
| hometica to Occa- | TO-247 | 0      | 0.48   | °C/W |
| Junction to Case  | TO-3PN | θις    | 0.44   | °C/W |

<sup>2.</sup> Pulse width limited by maximum junction temperature.

#### ■ **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub>=25°C, unless otherwise noted)

| PARAMETER                                       | SYMBOL              | TEST CONDITIONS  | MIN  | TYP   | MAX  | UNIT |  |
|---|---------------------|--|------|-------|------|------|--|
| OFF CHARACTERISTICS                             |                     |  |      |       |      |      |  |
| Collector-Emitter Breakdown Voltage             | BV <sub>CES</sub>   |  | 1200 |       |      | V    |  |
| Collector Cut-Off Current                       | I <sub>CES</sub>    | V <sub>CE</sub> =V <sub>CES</sub> , V <sub>GE</sub> =0V          |      |       | 5    | μΑ   |  |
| G-E Leakage Current                             | I <sub>GES</sub>    | V <sub>GE</sub> =V <sub>GES</sub> , V <sub>CE</sub> =0V          |      |       | ±250 | mA   |  |
| On Characteristics                              |                     |  |      |       |      |      |  |
| Gate to Emitter Threshold Voltage               | $V_{\text{GE(TH)}}$ | I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>          | 4.5  |       | 7.5  | V    |  |
| Collector to Emitter Saturation Voltage         | .,                  | I <sub>C</sub> =30A, V <sub>GE</sub> =15V                        |      | 1.82  | 2.1  | V    |  |
|   | $V_{CE(SAT)}$       | I <sub>C</sub> =30A, V <sub>GE</sub> =15V, T <sub>C</sub> =125°C |      | 2.0   |      | V    |  |
| DYNAMIC CHARACTERISTICS                         |                     |  |      |       |      |      |  |
| Input Capacitance                               | CIES                |  |      | 1690  |      | pF   |  |
| Output Capacitance                              | $C_OES$             | V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz                |      | 82    |      | pF   |  |
| Reverse Transfer Capacitance                    | C <sub>RES</sub>    |  |      | 52.7  |      | pF   |  |
| SWITCHING CHARACTERISTICS                       |                     |  |      |       |      |      |  |
| Total Gate Charge                               | $Q_{\mathrm{G}}$    |  |      | 138.3 |      | nC   |  |
| Gate-Emitter Charge                             | $Q_GE$              | V <sub>CE</sub> =600V, IC=30A, V <sub>GE</sub> =15V              |      | 17.1  |      | nC   |  |
| Gate-Collector Charge                           | $Q_{GC}$            |  |      | 99.3  |      | nC   |  |
| Turn-On Delay Time                              | t <sub>DON)</sub>   |  |      | 16.4  |      | ns   |  |
| Rise Time                                       | $t_R$               |  |      | 23    |      | ns   |  |
| Turn-Off Delay Time                             | t <sub>DOFF)</sub>  | Vcc=600V, Ic=30A, Rg=5Ω,   |      | 144.6 |      | ns   |  |
| Fall Time                                       | $t_{F}$             | V <sub>GE</sub> =0~15V, L=500uH                                  |      | 217.7 |      | ns   |  |
| Turn-On Switching Loss                          | Eon                 |  |      | 2.21  |      | mJ   |  |
| Turn-Off Switching Loss                         | E <sub>OFF</sub>    |  |      | 2.28  |      | mJ   |  |
| SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS |                     |  |      |       |      |      |  |
| Forward Voltage Drop                            | $V_{FM}$            | I <sub>F</sub> =30A  |      |       | 3.0  | V    |  |
| Reverse Recovery Time                           | t <sub>rr</sub>     | I <sub>F</sub> =30A,   |      | 53.7  |      | ns   |  |
| Reverse Recovery Charge                         | Qrr                 | dI/dt=100A/ <i>μ</i> S   |      | 1243  |      | nC   |  |

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